## **Electronic Supplementary Material (ESI)** for

## Exploiting monolayer MoSi<sub>2</sub>N<sub>4</sub>, WSi<sub>2</sub>N<sub>4</sub> and WGe<sub>2</sub>N<sub>4</sub> for efficient photocatalytic overall water splitting across a broad pH range

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Fig. S1 AIMD of MoSi2N4, WSi2N4, and WGe2N4



Fig. S2 The external potentials of (a) U<sub>e</sub> and (b) U<sub>h</sub> provided by MoSi<sub>2</sub>N<sub>4</sub>, WSi<sub>2</sub>N<sub>4</sub>, and WGe<sub>2</sub>N<sub>4</sub>, respectively, where the negative value indicates that there is no photocatalytic activity.



Fig. S3 Calculated imaginary part of dielectric function of MoSi<sub>2</sub>N<sub>4</sub>, WSi<sub>2</sub>N<sub>4</sub>, and WGe<sub>2</sub>N<sub>4</sub> using HSE06.



Fig. S4 The top and side view of (a) MoSi<sub>2</sub>N<sub>4</sub>, (b)WSi<sub>2</sub>N<sub>4</sub> and (c) WGe<sub>2</sub>N<sub>4</sub> of hydrogen atom adsorption, respectively.



Fig. S5 The top and side view of (a) V<sub>N</sub>-MoSi<sub>2</sub>N<sub>4</sub>, (b) V<sub>N</sub>-WSi<sub>2</sub>N<sub>4</sub> and (c) V<sub>N</sub>-WGe<sub>2</sub>N<sub>4</sub> of hydrogen atom adsorption, respectively.



Fig. S6 The free energy for OER on the surface of (a)  $MoSi_2N_4$ , (b)  $WSi_2N_4$ , and (c)  $WGe_2N_4$ , respectively.



Fig. S7 The free energy for HER in (a)  $MoSi_2N_4$ , (b)  $WSi_2N_4$ , and (c)  $WGe_2N_4$  with considering the N vacancy defects. Black line corresponds the conditions absent of light irradiation at pH = 4, 12, and 8, the red line denotes the provision of light at pH = 4, 12, and 8 for  $MoSi_2N_4$ ,  $WSi_2N_4$ , and  $WGe_2N_4$  respectively.